

1/1 DWPX - (C) The Thomson Corp.

AN - 2002-239538 [29]

TI - Reducing defects during the manufacture of semiconductor wafers, using compositions including surfactants and water where the amount of surfactant in the composition is less than the critical micelle concentration

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IN - LACHOWSKI JF

PN - WO200163365 A1 20010830 DW2002-29 G03F-007/32 Eng 15p \*

AP: 2001WO-US06119 20010226

- AU200138696 A 20010903 DW2002-29 Eng

FD: Based on WO200163365 A

AP: 2001AU-0038696 20010226

- US20020001780 A1 20020103 DW2002-29 G03F-007/42 Eng

AP: 2001US-0794643 20010226, Provisional 2000US-P185343 20000226

- EP1264216 A1 20021211 DW2003-01 G03F-007/32 Eng

FD: Based on WO200163365 A

AP: 2001EP-0911176 20010226, 2001WO-US06119 20010226

- JP2003524213 W 20030812 DW2003-55 G03F-007/32 Jpn 18p

FD: Based on WO200163365 A

AP: 2001JP-0562265 20010226, 2001WO-US06119 20010226

- KR2003034045 A 20030501 DW2003-57 G03F-007/32 Kor

AP: 2002KR-0711024 20020823

- US6670107 B2 20031230 DW2004-02 G03C-005/00 Eng

AP: 2001US-0794643 20010226, Provisional 2000US-P185343 20000226

- TW-558736 A 20031021 DW2004-24 H01L-021/00 Chi

AP: 2001TW-0104231 20010223

PR - 2000US-P185343 20000226; 2001US-0794643 20010226

DS - WO200163365

National States: AE AG AL AM AT AU AZ BA BB BG BR BY BZ CA CH CN CR CU CZ DE DK DM DZ EE ES FI GB GD GE GH GM HR HU ID IL IN IS JP KE KG KP KR KZ LC LK LR LS LT LU LV MA MD MG MK MN MW MX MZ NO NZ PL PT RO RU SD SE SG SI SK SL TJ TM TR TT TZ UA UG UZ VN YU ZA ZW  
Regional States: AT BE CH CY DE DK EA ES FI FR GB GH GM GR IE IT KE LS LU MC MW MZ NL OA PT SD SE SL SZ TR TZ UG ZW

- EP1264216

Regional States: AL AT BE CH CY DE DK ES FI FR GB GR IE IT LI LT LU LV MC MK NL PT RO SE SI TR

AB - WO2001063365 A

NOVELTY: A wafer is contacted with a composition including one or more surfactants and water. The amount of surfactant is less than the critical micelle concentration. The surfactant is selected from cationic surfactants or monoionic surfactants. The amount of surfactant is less than 1000ppm.

- DESCRIPTION: An INDEPENDENT CLAIM is included for a method of manufacturing an electronic device or wafer and a method of removing photoresist

- USE: In the manufacture of semiconductor wafers

- ADVANTAGE: Reduces number of defects in wafers, particularly those due to residual photoresist or photoresist residue remaining after development or stripping of the photoresist

UP - 2002-29

UE - 2002-29; 2003-01; 2003-55; 2003-57; 2004-02; 2004-24